

<b>FORM PTO-1449 (SUBSTITUTE)</b>  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b> (37 CFR 1.98(b))				Attorney Docket No.: P2001,0387 Appl. No.:  Applicant: GABRIELE FICHTL ET AL.  Filing Date: November 17, 2003 Group Art Unit:			
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
AL	A	5,871,659	2/16/99	Sakano et al.			
I	B	5,719,080	2/17/98	Kenney			
I	C	6,221,784 B1	4/24/01	Schmidt et al.			
I	D	5,998,821	12/7/99	Hieda et al.			
I	E	5,423,941	6/13/95	Komura et al.			
AL	F	6,583,020 B2	6/24/03	Uhlig et al.			
	G						
	H						
	I						
<b>FOREIGN PATENT DOCUMENT</b>							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
AL	J	00/54326	9/14/00	WIPO			
I	K	63240027	10/5/88	Japan			
I	L	10022271	1/23/98	Japan			
AL	M	0 819 786 A2	1/21/98	Europe			
	N						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
AL		Author not listed: "Process for Simultaneously Forming Poly/EPI Silicon Filled Deep and Shallow Isolation Trenches Having a CVD Oxide Cap", IBM Technical Disclosure Bulletin, IBM Corp., Vol. 33, No. 7, December 1990 pp. 388-392					
<b>EXAMINER</b> 				<b>DATE CONSIDERED</b> 05/28/04			